

IR-Lumineszenzdiode (940 nm) mit hoher Ausgangsleistung
High Power Infrared Emitter (940 nm)
Lead (Pb) Free Product - RoHS Compliant
SFH 4240



Wesentliche Merkmale

- Infrarot LED mit sehr hoher Ausgangsleistung
- Kurze Schaltzeiten
- Hohe Bestromung bei hohen Temperaturen möglich

Anwendungen

- Infrarotbeleuchtung für Kameras
- IR-Datenübertragung
- Sensorik

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Features

- High Power Infrared LED
- Short switching times
- High forward current allowed at high temperature

Applications

- Infrared Illumination for cameras
- IR Data Transmission
- Optical sensors

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ $I_e \text{ (mW/sr)}$
SFH 4240	Q65110A7513	≥ 10 (typ. 15)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}, T_{stg}	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Vorwärtsgleichstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 100\ \mu\text{s}$, $D = 0$ Surge current	I_{FSM}	1.5	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je $16\ \text{mm}^2$ Thermal resistance junction - ambient mounted on PC-board (FR4), padsize $16\ \text{mm}^2$ each	R_{thJA}	300	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	140	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\ \text{mA}$	λ_{peak}	950	nm
Centroid-Wellenlänge der Strahlung Centroid wavelength $I_F = 100\ \text{mA}$	$\lambda_{centroid}$	940	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\ \text{mA}$	$\Delta\lambda$	42	nm
Abstrahlwinkel Half angle	φ	± 60	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm^2

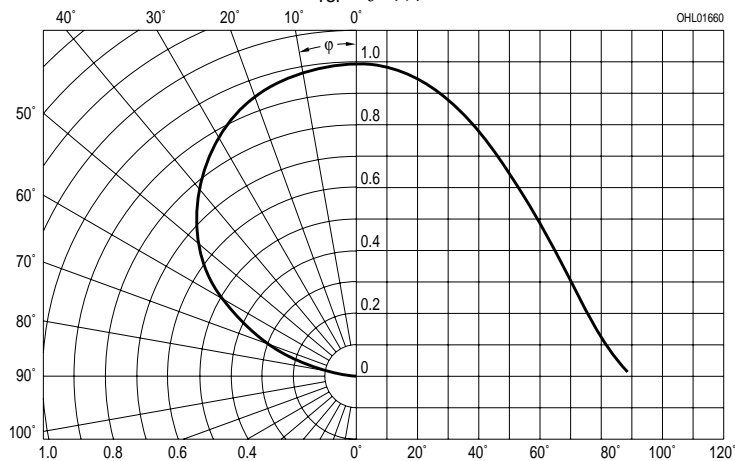
Kennwerte ($T_A = 25\text{ °C}$)
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$	t_r, t_f	11	ns
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$	V_F V_F	1.5 (< 1.8) 2.3 (< 3.0)	V V
Sperrstrom Reverse current	I_R	not designed for reverse operation	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	45	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 3	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.3	nm/K

Strahlstärke I_e in Achsrichtung¹⁾gemessen bei einem Raumwinkel $\Omega = 0.01$ sr**Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01$ sr

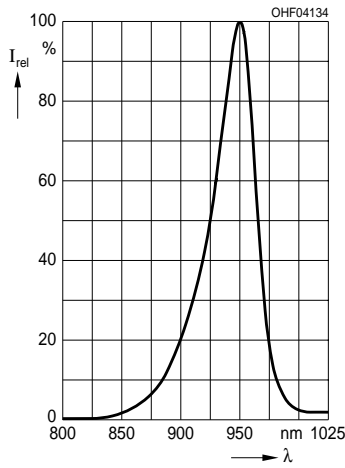
Bezeichnung Parameter	Symbol	Werte Values		Einheit Unit
		SFH 4240-R	SFH 4240-S	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$	10	16	mW/sr
	$I_{e \text{ max}}$	20	32	mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ}}$	100	120	mW/sr

¹⁾ Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) /
Only one group in one packing unit (variation lower 2:1)

Abstrahlcharakteristik**Radiation Characteristics $I_{\text{rel}} = f(\varphi)$** 

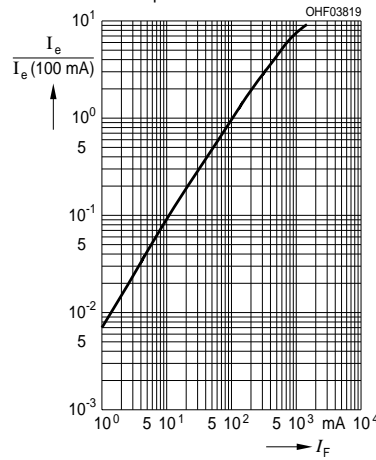
Relative Spectral Emission

$I_{rel} = f(\lambda)$



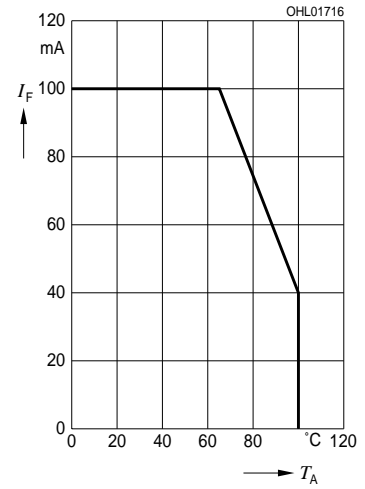
Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse, $t_p = 25 \mu\text{s}$



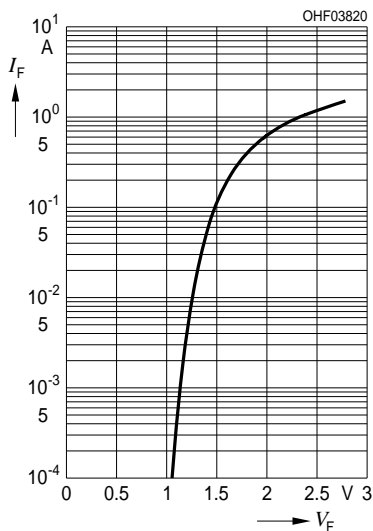
Max. Permissible Forward Current

$I_F = f(T_A), R_{thJA} = 300 \text{ K/W}$



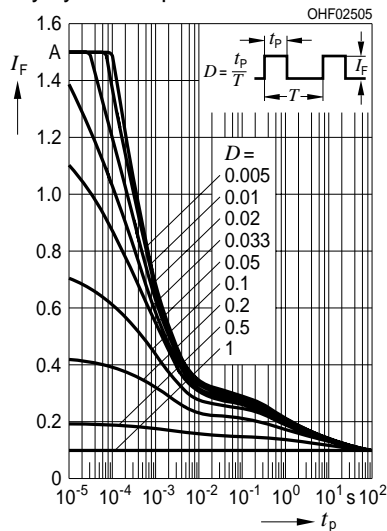
Forward Current $I_F = f(V_F)$

Single pulse, $t_p = 25 \mu\text{s}$

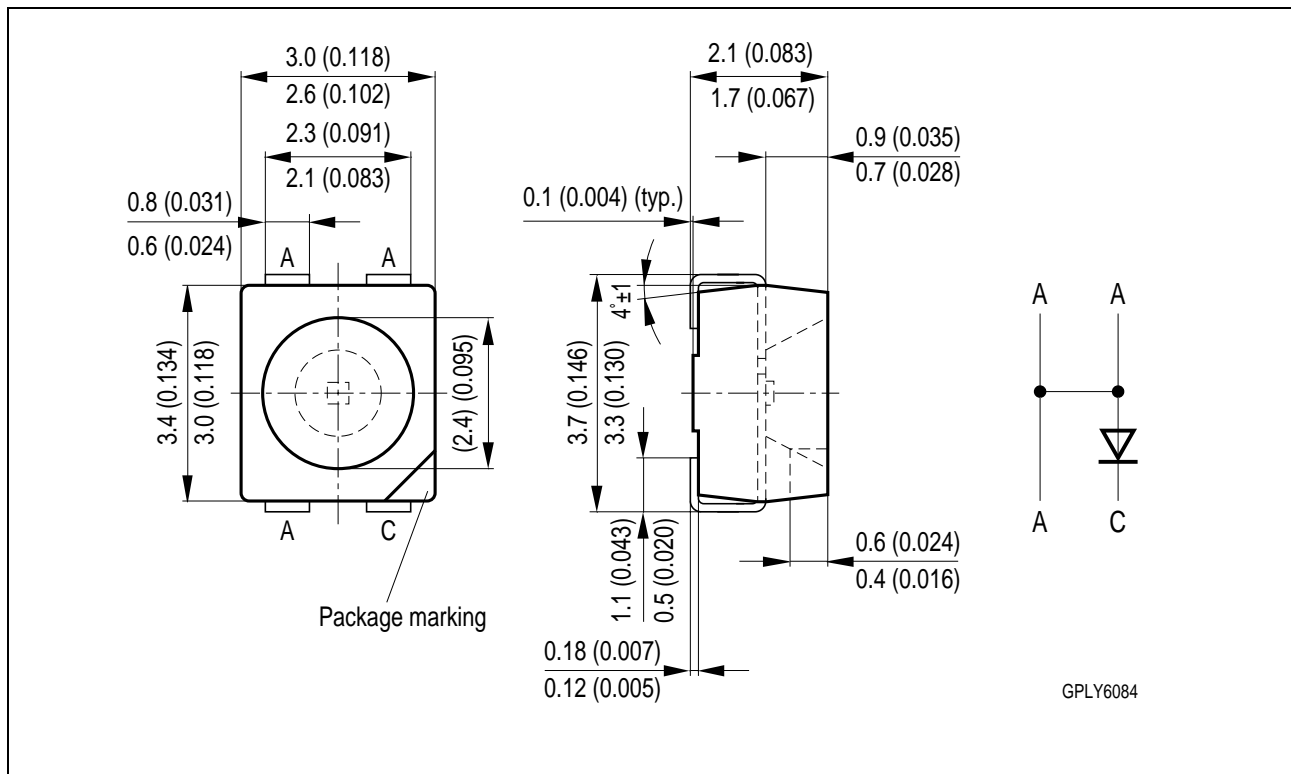


Permissible Pulse Handling Capability $I_F = f(\tau), T_A = 25 \text{ °C}$,

duty cycle $D = \text{parameter}$



Maßzeichnung Package Outlines

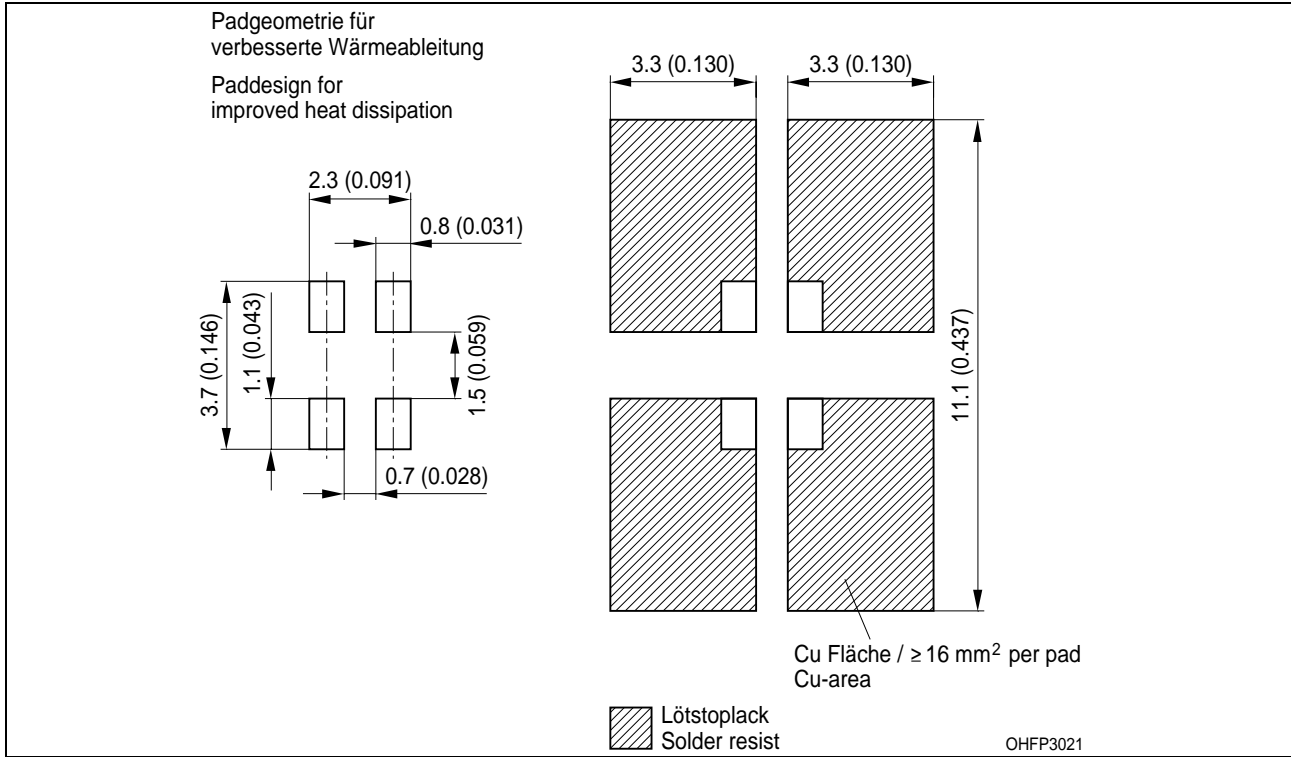


Maße in mm (inch) / Dimensions in mm (inch).

Gehäuse / Package	Power TOPLED [®] , klarer Verguss / Power TOPLED [®] , clear resin
Anschlussbelegung Pin configuration	Kathode: abgeschrägte Ecke Cathode: beveled edge

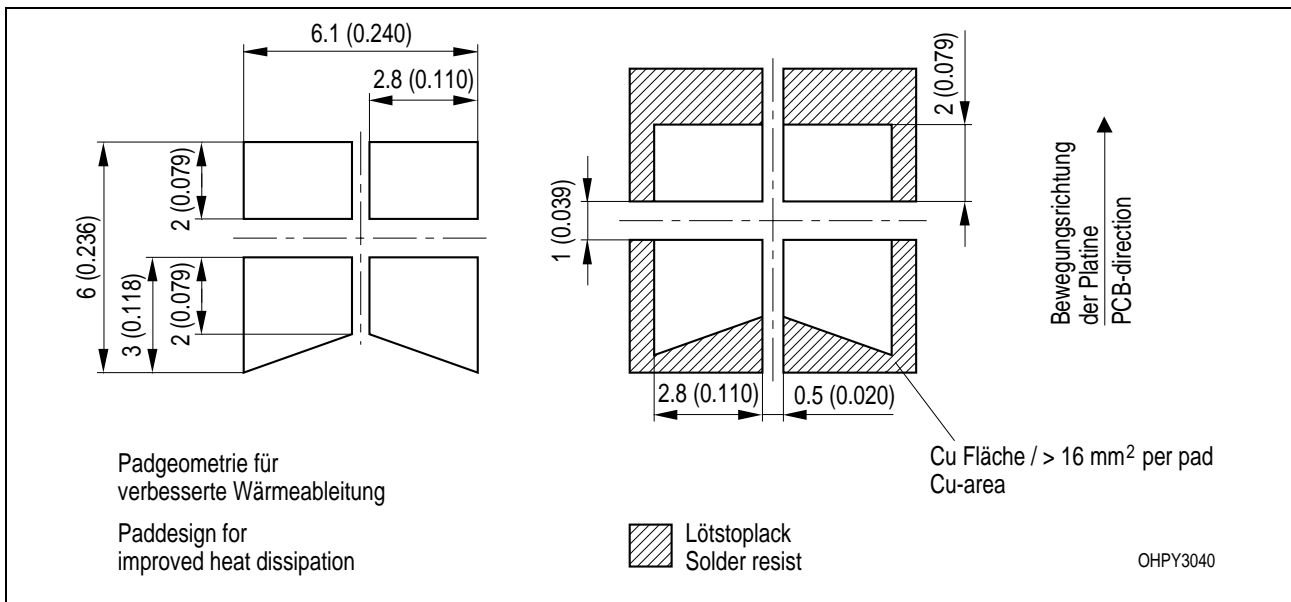
Empfohlenes Lötpad-Design
Recommended Solder Pad Design

Reflow Lötén
Reflow Soldering



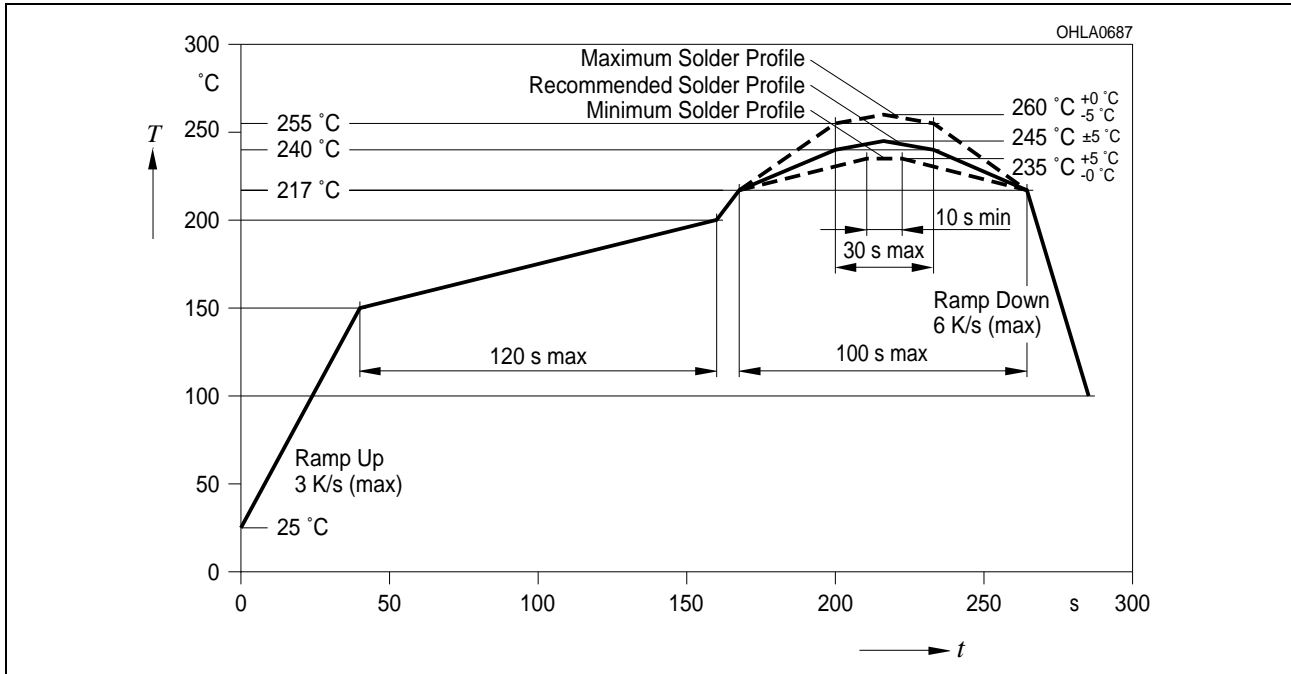
Empfohlenes Lötpad-Design
Recommended Solder Pad Design

Wellenlötén TTW
TTW Soldering



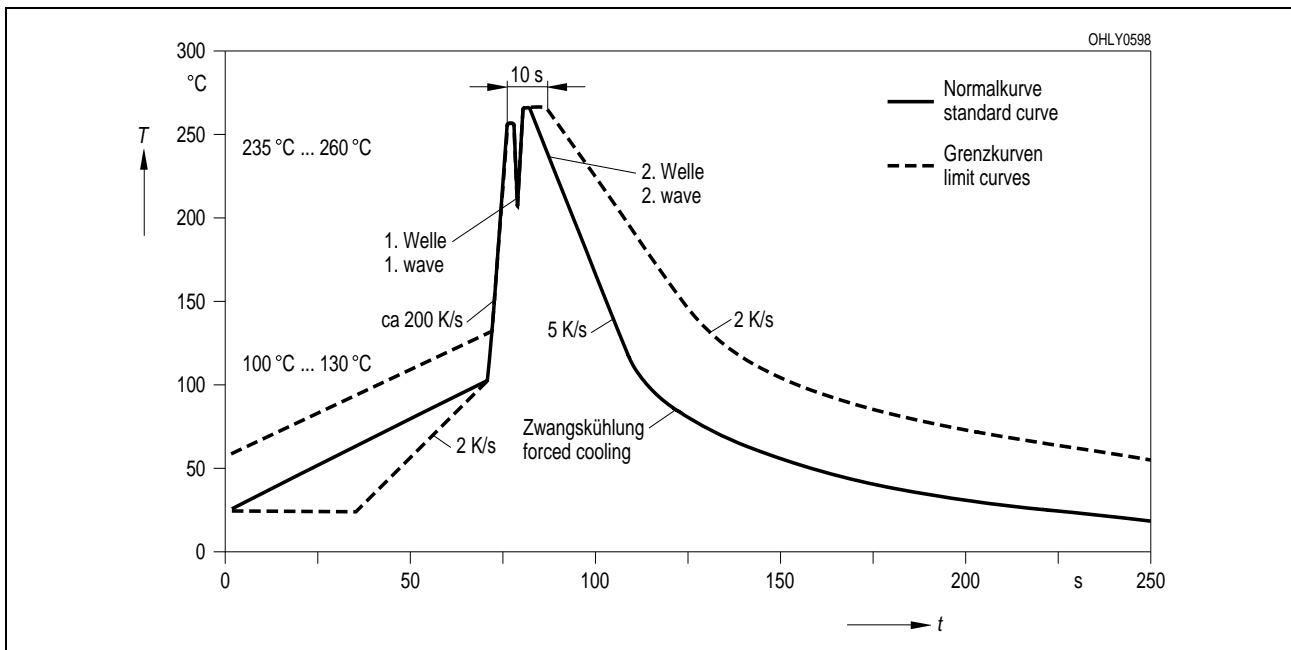
Lötbedingungen
Soldering Conditions
Reflow Lötprofil für bleifreies Löt
Reflow Soldering Profile for lead free soldering

Vorbehandlung nach JEDEC Level 2
 Preconditioning acc. to JEDEC Level 2
 (nach J-STD-020C)
 (acc. to J-STD-020C)



Wellenlötten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



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EU RoHS and China RoHS compliant product



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